

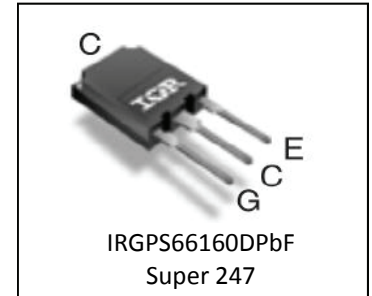
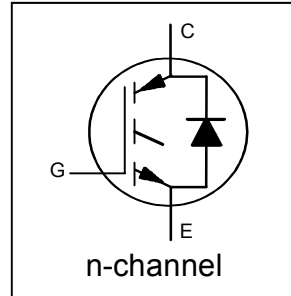


**THE DATASHEET OF  
IRGPS66160DPBF**



*Insulated Gate Bipolar Transistor with Ultrafast Soft Recovery Diode*

$V_{CES} = 600V$
$I_C = 160A, T_C = 100^\circ C$
$t_{SC} \geq 5\mu s, T_{J(max)} = 175^\circ C$
$V_{CE(ON)} \text{ typ.} = 1.65V @ I_C = 120A$



G	C	E
Gate	Collector	Emitter

**Applications**

- Welding
- H Bridge Converters

Features	Benefits
Low $V_{CE(ON)}$ and Switching Losses	High Efficiency in a Wide Range of Applications
Optimized Diode for Full Bridge Hard Switch Converters	Optimized for Welding and H Bridge Converters
Square RBSOA and Maximum Temperature of $175^\circ C$	Improved Reliability due to Rugged Hard Switching Performance and High Power Capability
$5\mu s$ Short Circuit	Enables Short Circuit Protection Operation
Positive $V_{CE(ON)}$ Temperature Co-efficient	Excellent Current Sharing in Parallel Operation
Lead-free, RoHS compliant	Environmentally friendly

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRGPS66160DPbF	Super 247	Tube	25	IRGPS66160DPbF

**Absolute Maximum Ratings**

	Parameter	Max.	Units
$V_{CES}$	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	240	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	160	
$I_{CM}$	Pulse Collector Current, $V_{GE} = 15V$	360	
$I_{LM}$	Clamped Inductive Load Current, $V_{GE} = 20V$ ①	480	
$I_{FRM} @ T_C = 100^\circ C$	Diode Repetitive Peak Forward Current④⑥	80	
$I_{FM}$	Diode Maximum Forward Current ④	480	W
$V_{GE}$	Continuous Gate-to-Emitter Voltage	$\pm 20$	
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	750	°C
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	375	
$T_J$ $T_{STG}$	Operating Junction and Storage Temperature Range	-40 to +175	300 (0.063 in. (1.6mm) from case)
	Soldering Temperature, for 10 sec.		

**Thermal Resistance**

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance Junction-to-Case-(each IGBT) ②	—	—	0.20	°C/W
$R_{\theta JC}$ (Diode)	Thermal Resistance Junction-to-Case-(each Diode) ②	—	—	1.37	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink (flat, greased surface)	—	0.24	—	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (typical socket mount)	—	—	40	

**Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)**

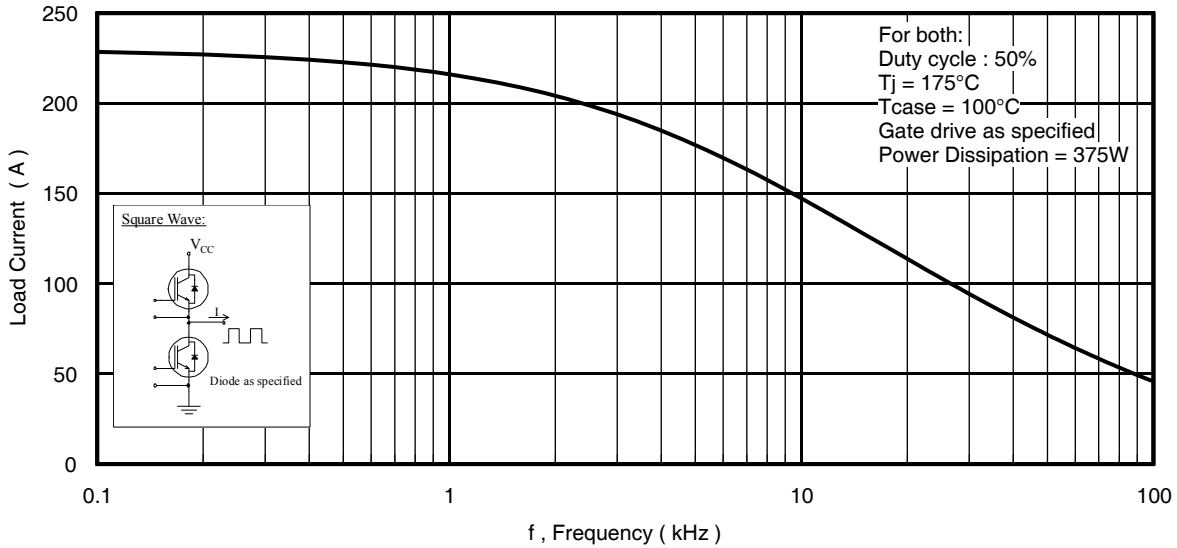
	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)CES</sub>	Collector-to-Emitter Breakdown Voltage	600	—	—	V	V <sub>GE</sub> = 0V, I <sub>C</sub> = 100μA ③
ΔV <sub>(BR)CES</sub> /ΔT <sub>J</sub>	Temperature Coeff. of Breakdown Voltage	—	0.54	—	V/°C	V <sub>GE</sub> = 0V, I <sub>C</sub> = 4.0mA (25°C-175°C)
V <sub>CE(on)</sub>	Collector-to-Emitter Saturation Voltage	—	1.65	1.95	V	I <sub>C</sub> = 120A, V <sub>GE</sub> = 15V, T <sub>J</sub> = 25°C
		—	1.95	—		I <sub>C</sub> = 120A, V <sub>GE</sub> = 15V, T <sub>J</sub> = 150°C
		—	2.0	—		I <sub>C</sub> = 120A, V <sub>GE</sub> = 15V, T <sub>J</sub> = 175°C
V <sub>GE(th)</sub>	Gate Threshold Voltage	4.0	—	6.5	V	V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 5.6mA
ΔV <sub>GE(th)</sub> /ΔT <sub>J</sub>	Threshold Voltage Temperature Coeff.	—	-16	—	mV/°C	V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 5.6mA (25°C-175°C)
g <sub>fe</sub>	Forward Transconductance	—	86	—	S	V <sub>CE</sub> = 50V, I <sub>C</sub> = 120A, PW = 20μs
I <sub>CES</sub>	Collector-to-Emitter Leakage Current	—	1.0	150	μA	V <sub>GE</sub> = 0V, V <sub>CE</sub> = 600V
		—	2000	—		V <sub>GE</sub> = 0V, V <sub>CE</sub> = 600V, T <sub>J</sub> = 175°C
I <sub>GES</sub>	Gate-to-Emitter Leakage Current	—	—	±400	nA	V <sub>GE</sub> = ±20V
V <sub>F</sub>	Diode Forward Voltage Drop	—	1.80	2.60	V	I <sub>F</sub> = 24A
		—	1.30	—		I <sub>F</sub> = 24A, T <sub>J</sub> = 175°C

**Switching Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)**

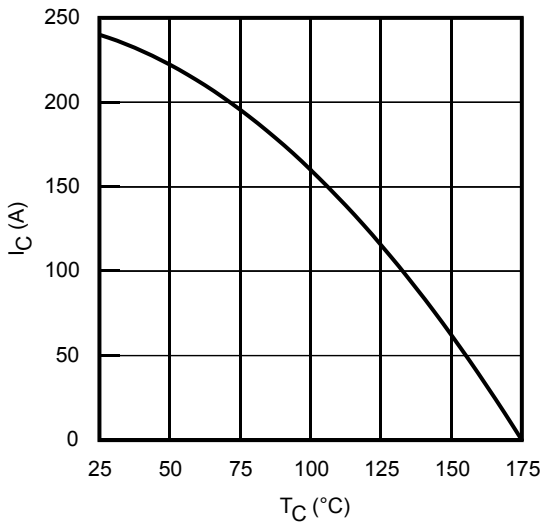
	Parameter	Min.	Typ.	Max	Units	Conditions
Q <sub>g</sub>	Total Gate Charge (turn-on)	—	220	—	nC	I <sub>C</sub> = 120A V <sub>GE</sub> = 15V V <sub>CC</sub> = 400V
Q <sub>ge</sub>	Gate-to-Emitter Charge (turn-on)	—	60	—		
Q <sub>gc</sub>	Gate-to-Collector Charge (turn-on)	—	90	—		
E <sub>on</sub>	Turn-On Switching Loss	—	4470	—	μJ	I <sub>C</sub> = 120A, V <sub>CC</sub> = 400V, V <sub>GE</sub> =15V R <sub>G</sub> = 4.7Ω, L = 66μH, T <sub>J</sub> = 25°C
E <sub>off</sub>	Turn-Off Switching Loss	—	3430	—		
E <sub>total</sub>	Total Switching Loss	—	7900	—		
t <sub>d(on)</sub>	Turn-On delay time	—	80	—	ns	Energy losses include tail & diode reverse recovery ⑤
t <sub>r</sub>	Rise time	—	75	—		
t <sub>d(off)</sub>	Turn-Off delay time	—	190	—		
t <sub>f</sub>	Fall time	—	40	—		
E <sub>on</sub>	Turn-On Switching Loss	—	5360	—		
E <sub>off</sub>	Turn-Off Switching Loss	—	4390	—	μJ	I <sub>C</sub> = 120A, V <sub>CC</sub> = 400V, V <sub>GE</sub> =15V R <sub>G</sub> = 4.7Ω, L = 66μH, T <sub>J</sub> = 175°C
E <sub>total</sub>	Total Switching Loss	—	9750	—		
t <sub>d(on)</sub>	Turn-On delay time	—	80	—		
t <sub>r</sub>	Rise time	—	130	—	ns	Energy losses include tail & diode reverse recovery ⑤
t <sub>d(off)</sub>	Turn-Off delay time	—	260	—		
t <sub>f</sub>	Fall time	—	90	—		
C <sub>ies</sub>	Input Capacitance	—	7660	—	pF	V <sub>GE</sub> = 0V V <sub>CC</sub> = 30V f = 1.0MHz
C <sub>oes</sub>	Output Capacitance	—	470	—		
C <sub>res</sub>	Reverse Transfer Capacitance	—	250	—		
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				T <sub>J</sub> = 175°C, I <sub>C</sub> = 480A V <sub>CC</sub> = 480V, V <sub>p</sub> ≤ 600V V <sub>GE</sub> = +20V to 0V
SCSOA	Short Circuit Safe Operating Area	5	—	—	μs	T <sub>J</sub> = 150°C, V <sub>CC</sub> = 400V, V <sub>p</sub> ≤ 600V V <sub>GE</sub> = +15V to 0V
E <sub>rec</sub>	Reverse Recovery Energy of the Diode	—	420	—	μJ	T <sub>J</sub> = 175°C
t <sub>rr</sub>	Diode Reverse Recovery Time	—	95	—	ns	V <sub>CC</sub> = 400V, I <sub>F</sub> = 24A, V <sub>GE</sub> = 15V
I <sub>rr</sub>	Peak Reverse Recovery Current	—	34	—	A	R <sub>G</sub> = 4.7Ω, L=200μH, L <sub>s</sub> =150nH

**Notes:**

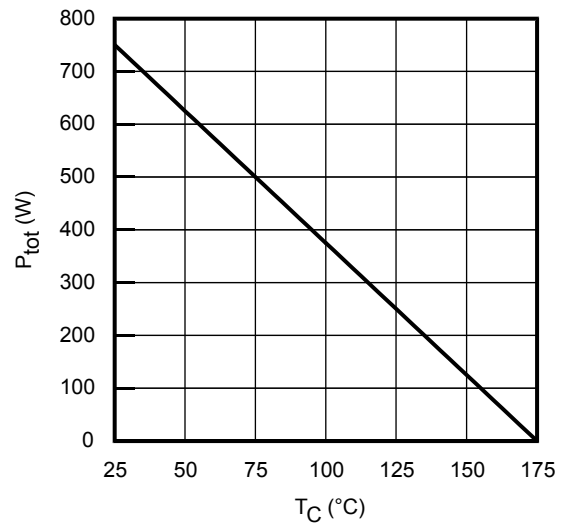
- ① V<sub>CC</sub> = 80% (V<sub>CES</sub>), V<sub>GE</sub> = 20V, R<sub>G</sub> = 4.7Ω, L=66μH.
- ② R<sub>θ</sub> is measured at T<sub>J</sub> of approximately 90°C.
- ③ Refer to AN-1086 for guidelines for measuring V<sub>(BR)CES</sub> safely.
- ④ Pulse width limited by max. junction temperature.
- ⑤ Values influenced by parasitic L and C in measurement.
- ⑥ f<sub>sw</sub> = 40KHz, refer to figure 26.



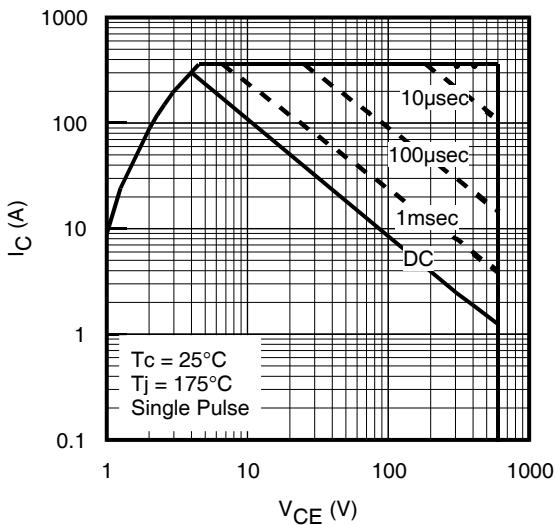
**Fig. 1 - Typical Load Current vs. Frequency**  
 (Load Current =  $I_{RMS}$  of fundamental)



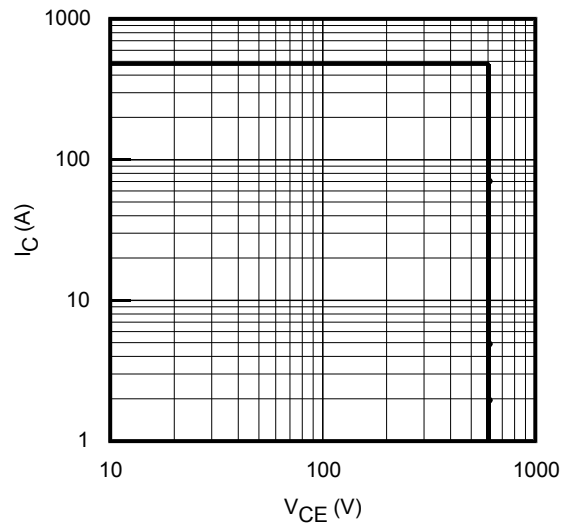
**Fig. 2 - Maximum DC Collector Current vs. Case Temperature**



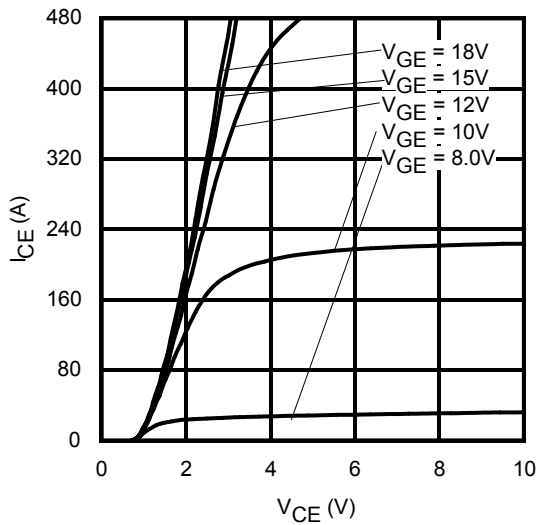
**Fig. 3 - Power Dissipation vs. Case Temperature**



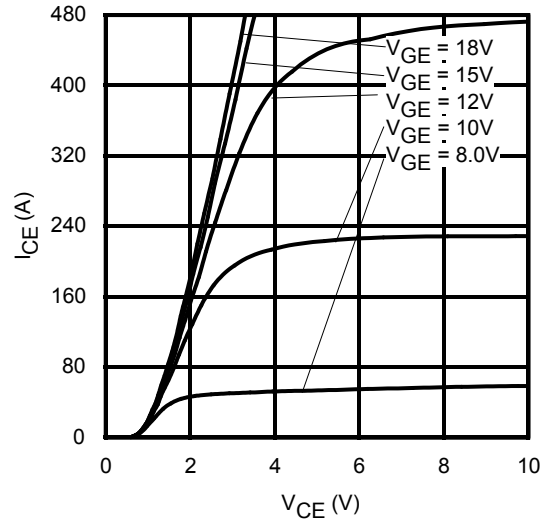
**Fig. 4 - Forward SOA**  
 $T_C = 25^\circ\text{C}$ ;  $T_j \leq 175^\circ\text{C}$ ;  $V_{GE} = 15\text{V}$



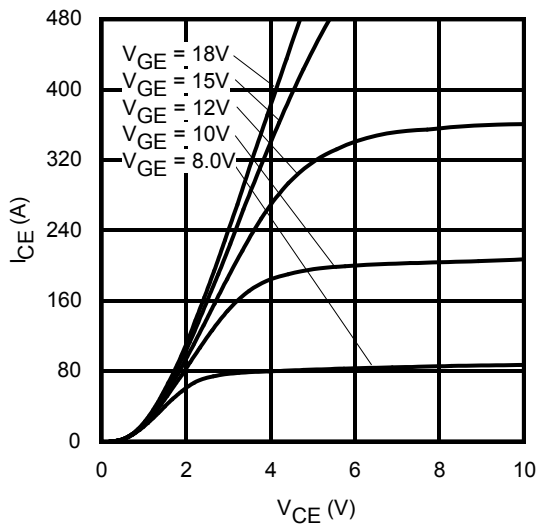
**Fig. 5 - Reverse Bias SOA**  
 $T_j = 175^\circ\text{C}$ ;  $V_{GE} = 20\text{V}$



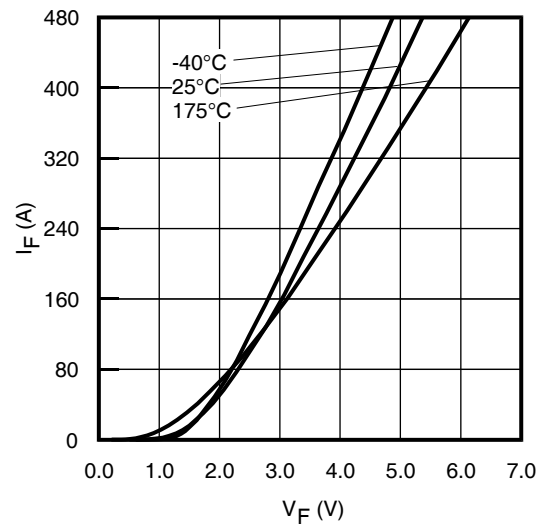
**Fig. 6 - Typ. IGBT Output Characteristics**  
 $T_J = -40^\circ\text{C}$ ;  $t_p = 20\mu\text{s}$



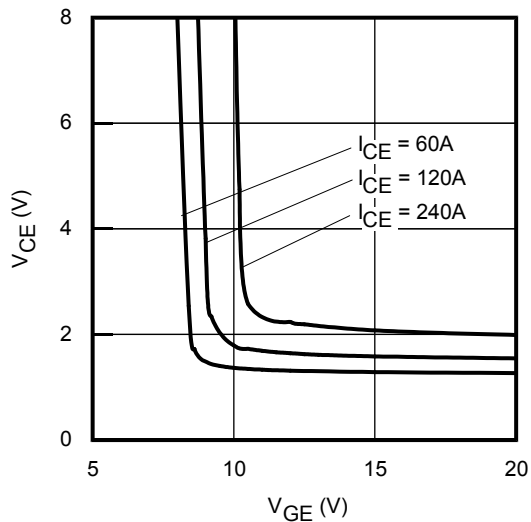
**Fig. 7 - Typ. IGBT Output Characteristics**  
 $T_J = 25^\circ\text{C}$ ;  $t_p = 20\mu\text{s}$



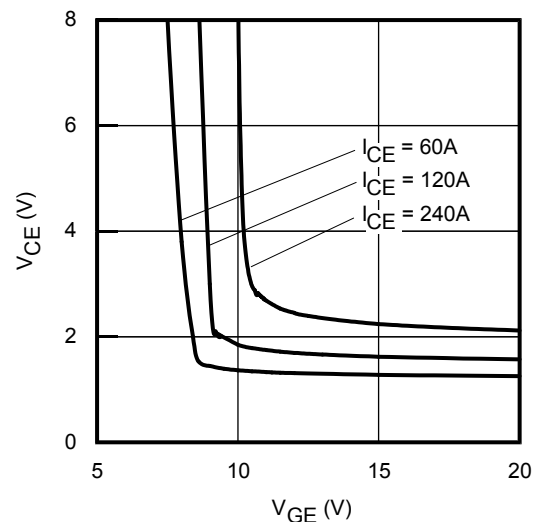
**Fig. 8 - Typ. IGBT Output Characteristics**  
 $T_J = 175^\circ\text{C}$ ;  $t_p = 20\mu\text{s}$



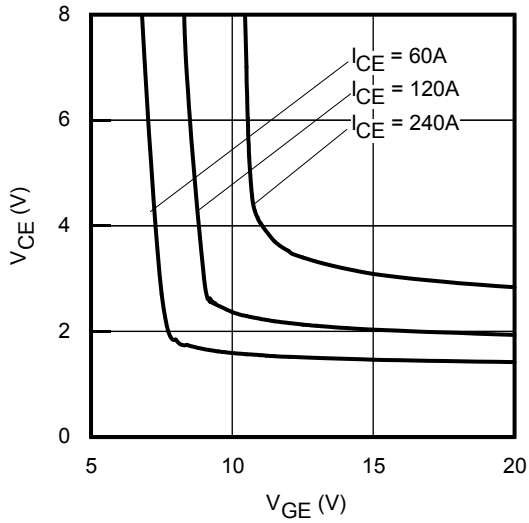
**Fig. 9 - Typ. Diode Forward Voltage Drop Characteristics**



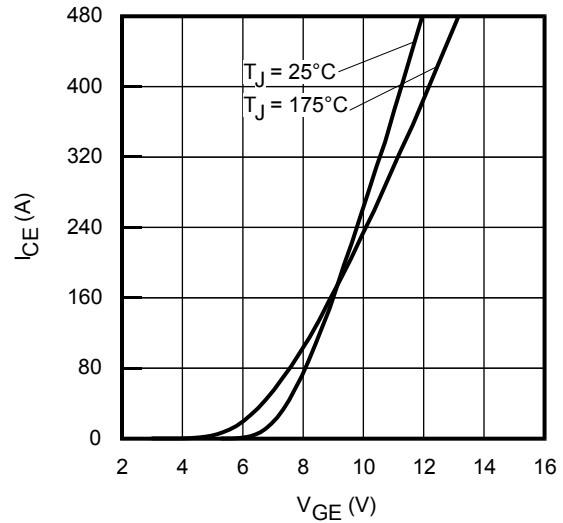
**Fig. 10 - Typical  $V_{CE}$  vs.  $V_{GE}$**   
 $T_J = -40^\circ\text{C}$



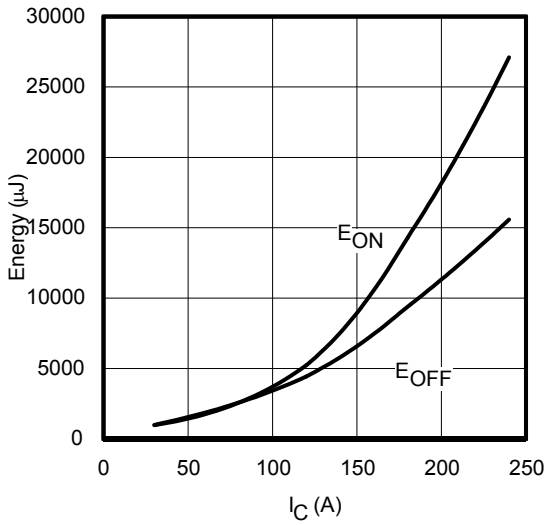
**Fig. 11 - Typical  $V_{CE}$  vs.  $V_{GE}$**   
 $T_J = 25^\circ\text{C}$



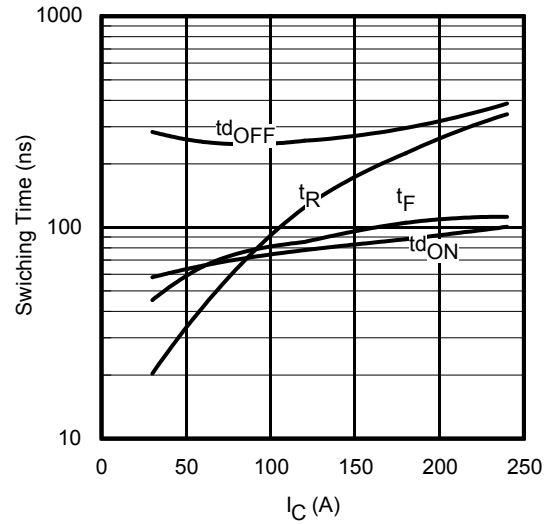
**Fig. 12** - Typical  $V_{CE}$  vs.  $V_{GE}$   
 $T_J = 175^\circ\text{C}$



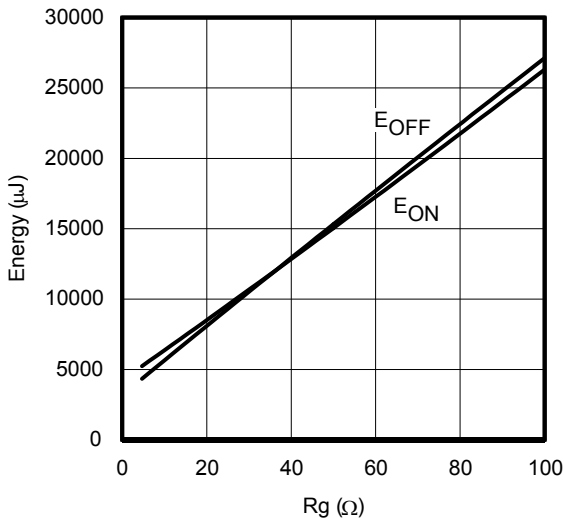
**Fig. 13** - Typ. Transfer Characteristics  
 $V_{CE} = 50\text{V}$ ;  $t_p = 20\mu\text{s}$



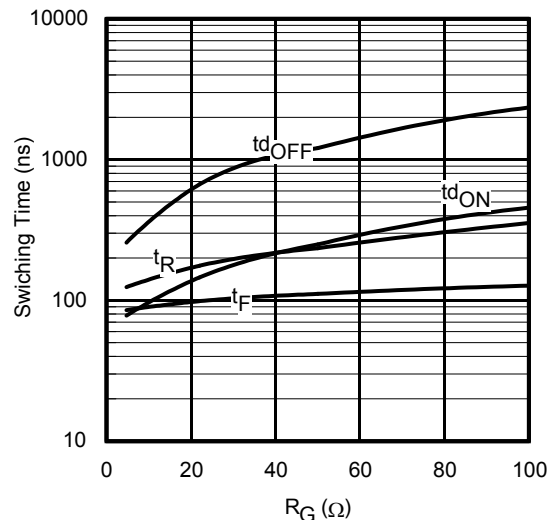
**Fig. 14** - Typ. Energy Loss vs.  $I_C$   
 $T_J = 175^\circ\text{C}$ ;  $V_{CE} = 400\text{V}$ ,  $R_G = 4.7\ \Omega$ ;  $V_{GE} = 15\text{V}$



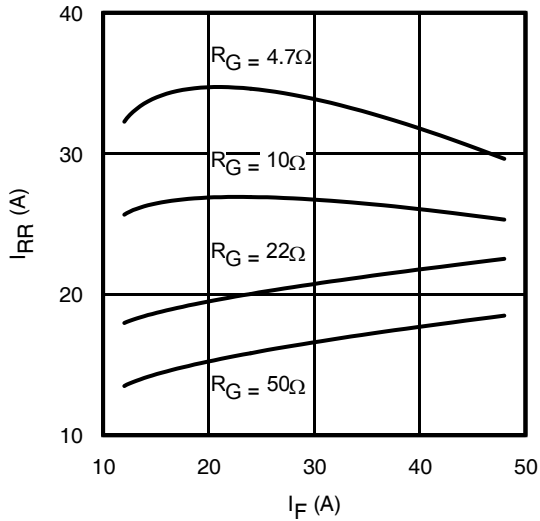
**Fig. 15** - Typ. Switching Time vs.  $I_C$   
 $T_J = 175^\circ\text{C}$ ;  $V_{CE} = 400\text{V}$ ,  $R_G = 4.7\ \Omega$ ;  $V_{GE} = 15\text{V}$



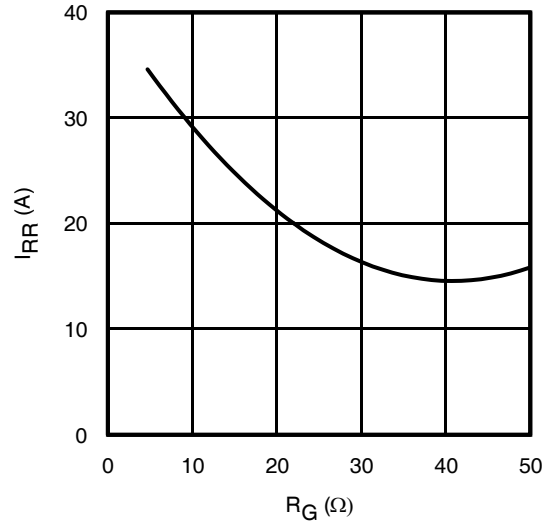
**Fig. 16** - Typ. Energy Loss vs.  $R_G$   
 $T_J = 175^\circ\text{C}$ ;  $V_{CE} = 400\text{V}$ ,  $I_{CE} = 120\text{A}$ ;  $V_{GE} = 15\text{V}$



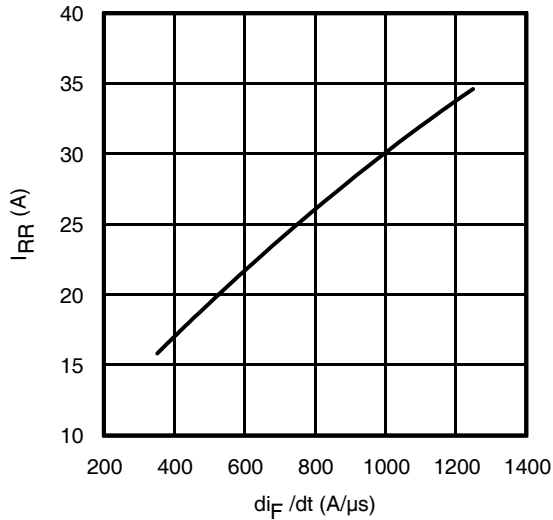
**Fig. 17** - Typ. Switching Time vs.  $R_G$   
 $T_J = 175^\circ\text{C}$ ;  $V_{CE} = 400\text{V}$ ,  $I_{CE} = 120\text{A}$ ;  $V_{GE} = 15\text{V}$



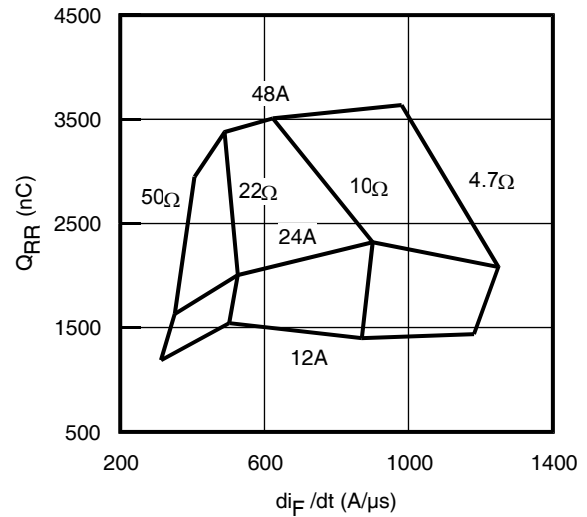
**Fig. 18** - Typ. Diode  $I_{RR}$  vs.  $I_F$   
 $T_J = 175^\circ\text{C}$



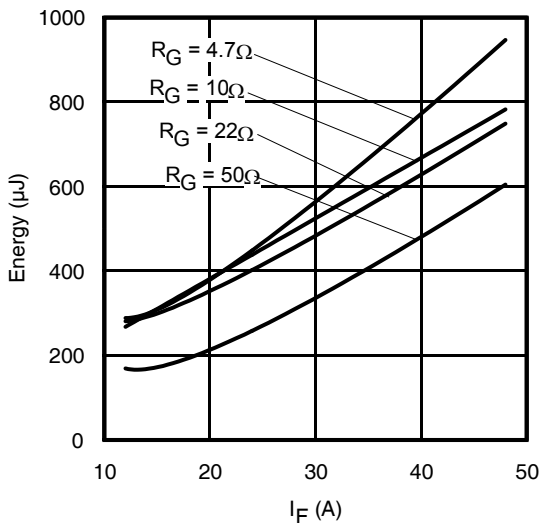
**Fig. 19** - Typ. Diode  $I_{RR}$  vs.  $R_G$   
 $T_J = 175^\circ\text{C}$



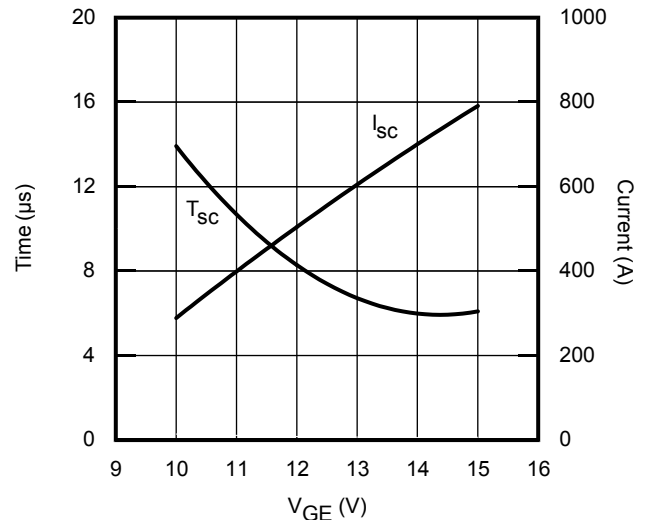
**Fig. 20** - Typ. Diode  $I_{RR}$  vs.  $di_F/dt$   
 $V_{CC} = 400\text{V}; V_{GE} = 15\text{V}; I_F = 24\text{A}; T_J = 175^\circ\text{C}$



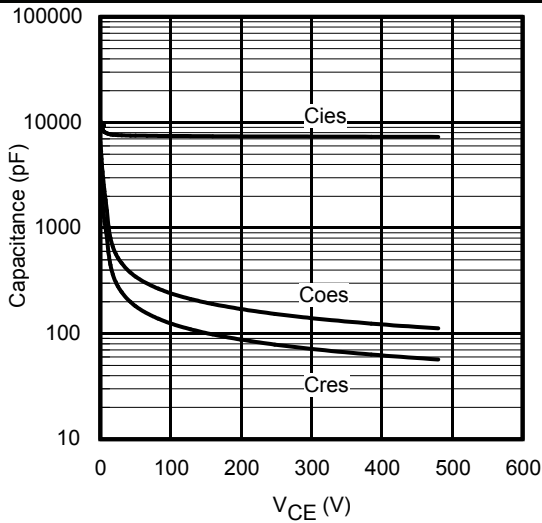
**Fig. 21** - Typ. Diode  $Q_{RR}$  vs.  $di_F/dt$   
 $V_{CC} = 400\text{V}; V_{GE} = 15\text{V}; T_J = 175^\circ\text{C}$



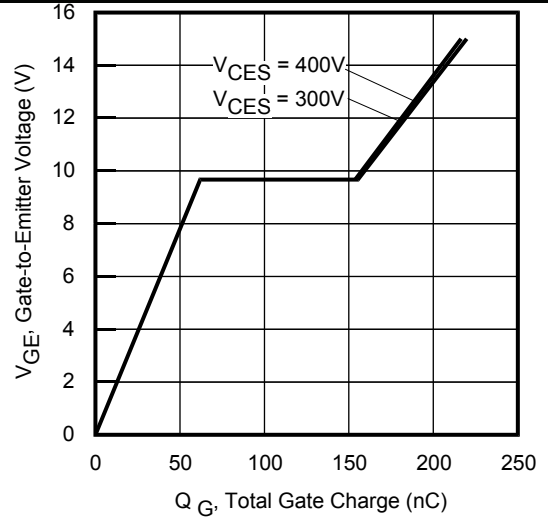
**Fig. 22** - Typ. Diode  $E_{RR}$  vs.  $I_F$   
 $T_J = 175^\circ\text{C}$



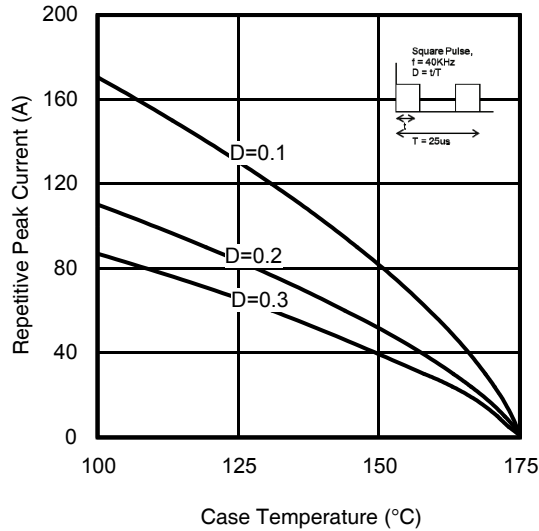
**Fig. 23** -  $V_{GE}$  vs. Short Circuit Time  
 $V_{CC} = 400\text{V}; T_C = 150^\circ\text{C}$



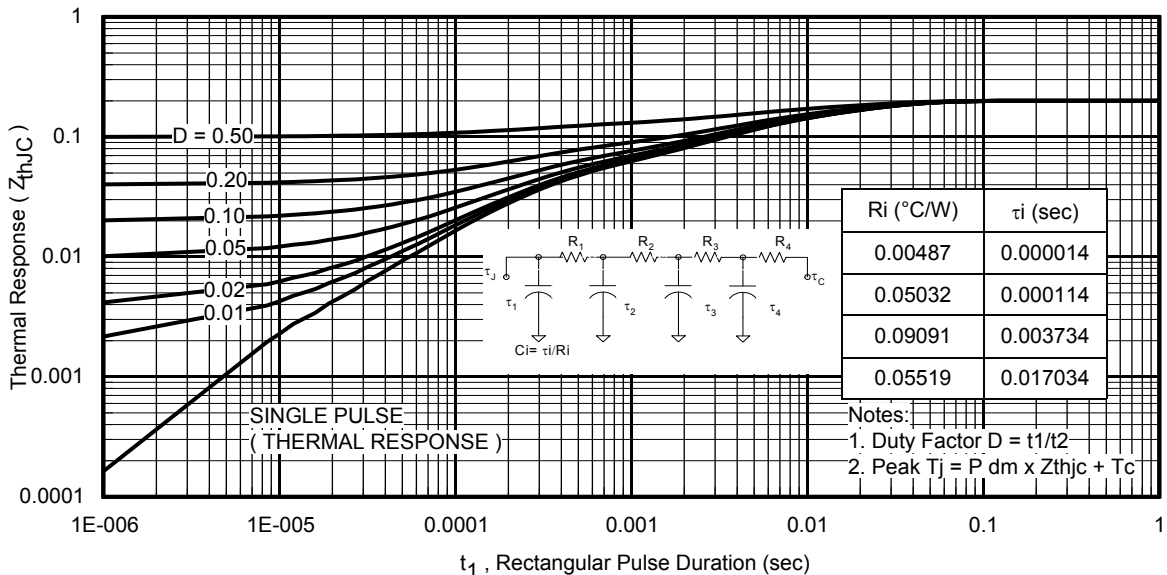
**Fig. 24** - Typ. Capacitance vs.  $V_{CE}$   
 $V_{GE} = 0V$ ;  $f = 1MHz$



**Fig. 25** - Typical Gate Charge vs.  $V_{GE}$   
 $I_{CE} = 120A$



**Fig 26.** Maximum Diode Repetitive Forward Peak Current vs. Case Temperature



**Fig. 27** - Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

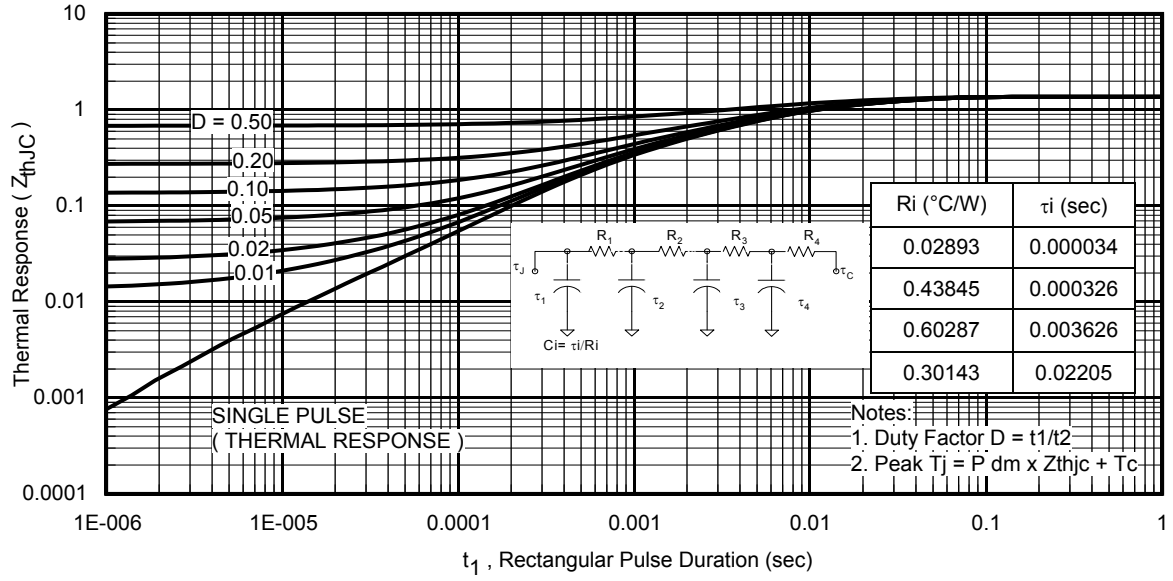
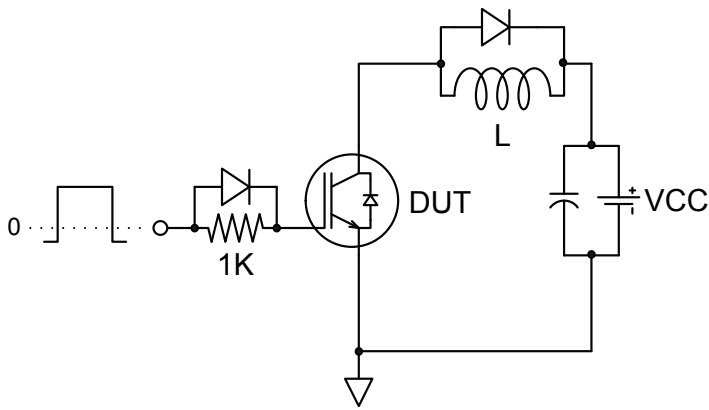
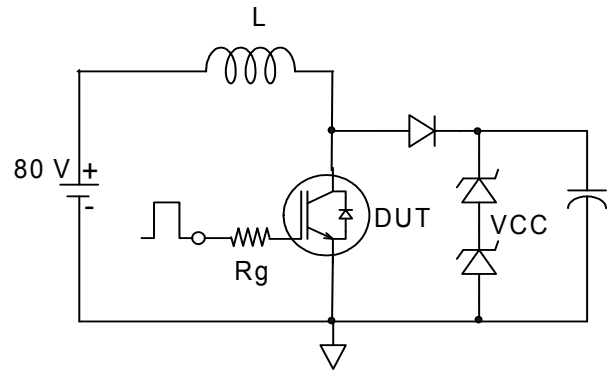


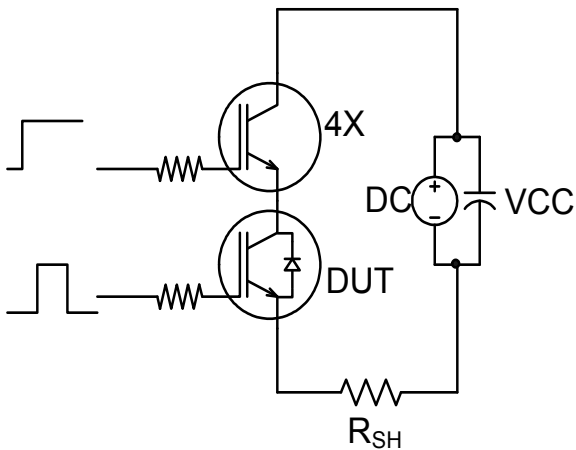
Fig. 28 - Maximum Transient Thermal Impedance, Junction-to-Case (DIODE)



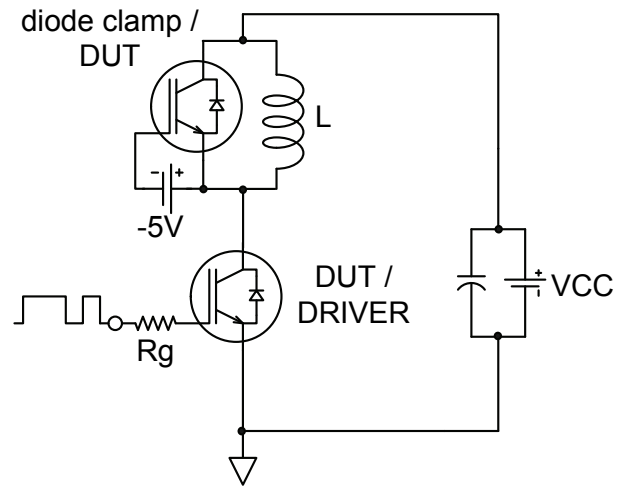
**Fig.C.T.1 - Gate Charge Circuit (turn-off)**



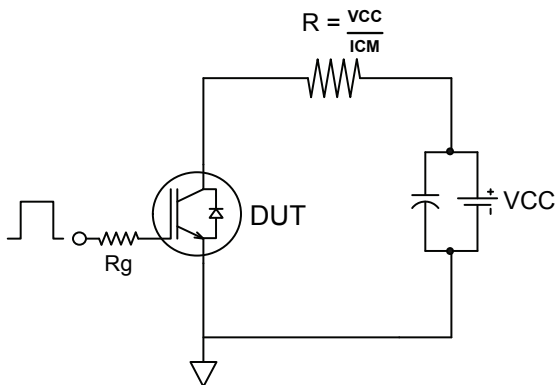
**Fig.C.T.2 - RBSOA Circuit**



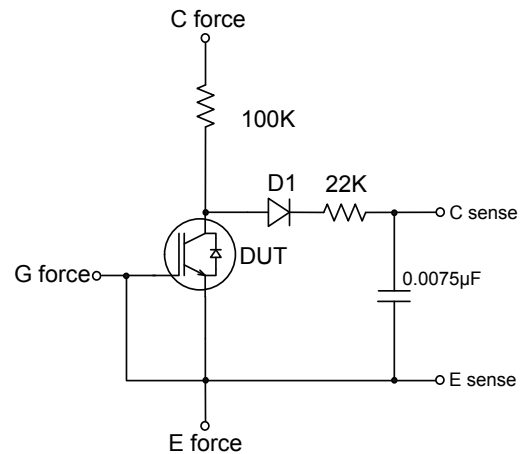
**Fig.C.T.3 - S.C. SOA Circuit**



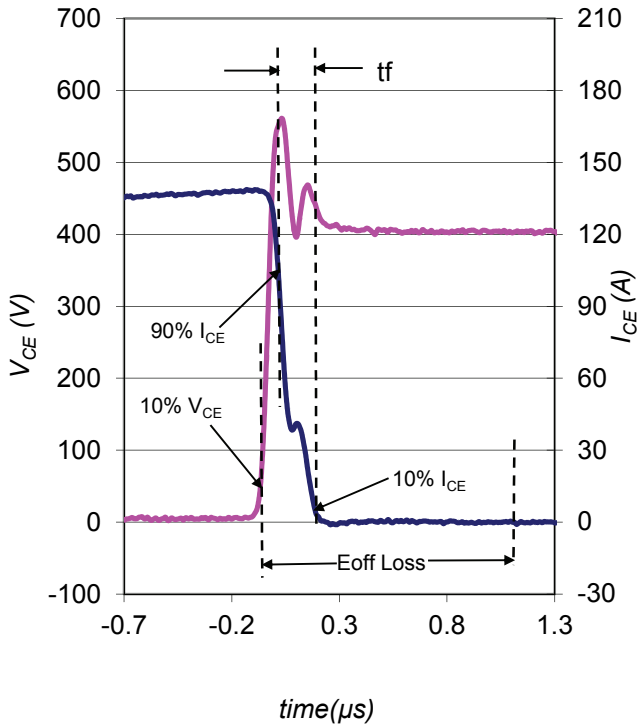
**Fig.C.T.4 - Switching Loss Circuit**



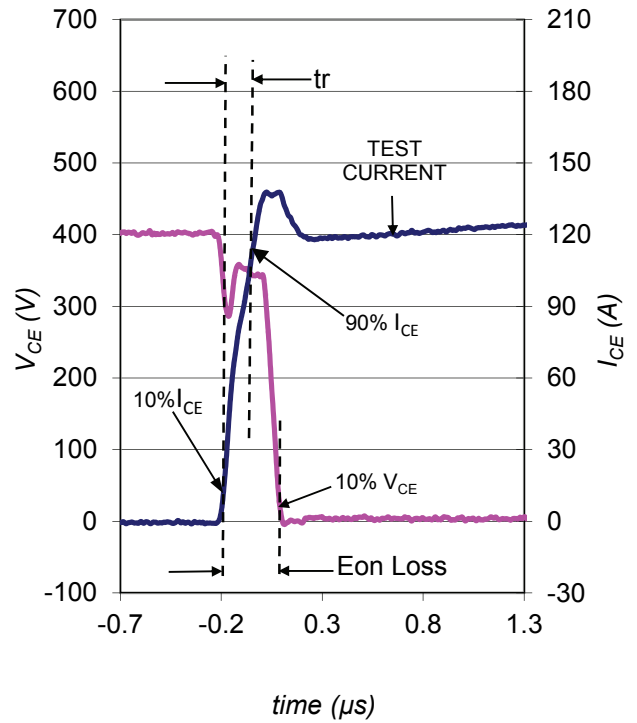
**Fig.C.T.5 - Resistive Load Circuit**



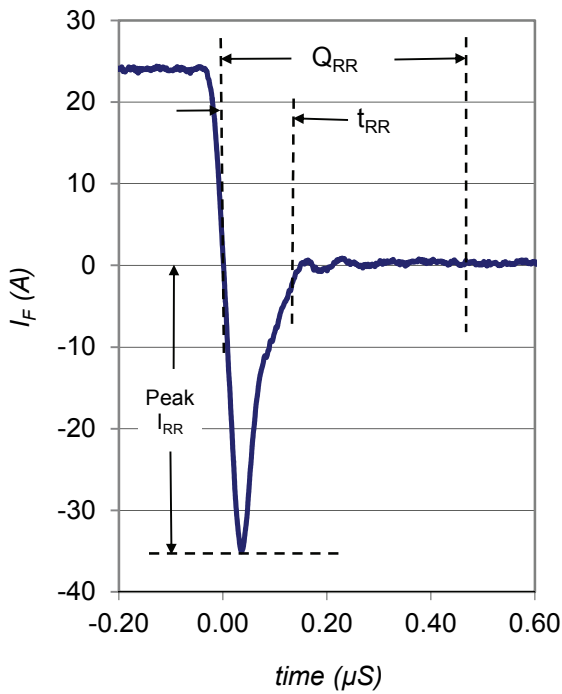
**Fig.C.T.6 - BVCES Filter Circuit**



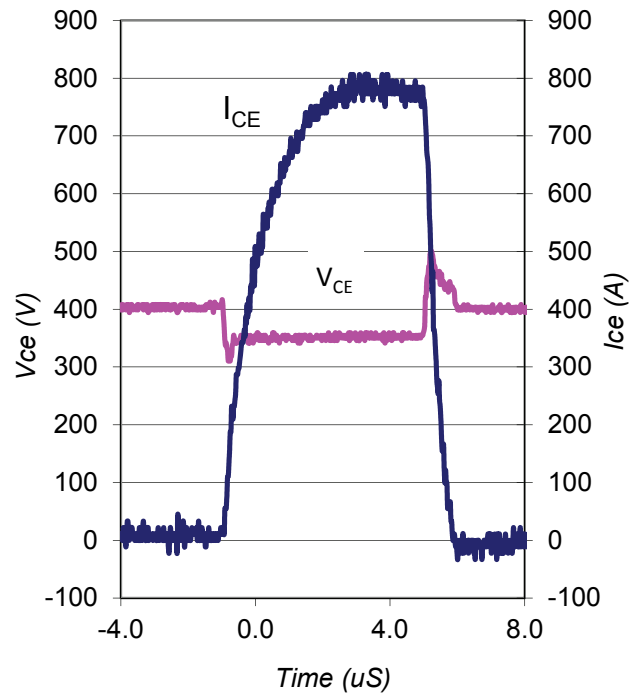
**Fig. WF1** - Typ. Turn-off Loss Waveform  
@  $T_J = 175^\circ\text{C}$  using Fig. CT.4



**Fig. WF2** - Typ. Turn-on Loss Waveform  
@  $T_J = 175^\circ\text{C}$  using Fig. CT.4



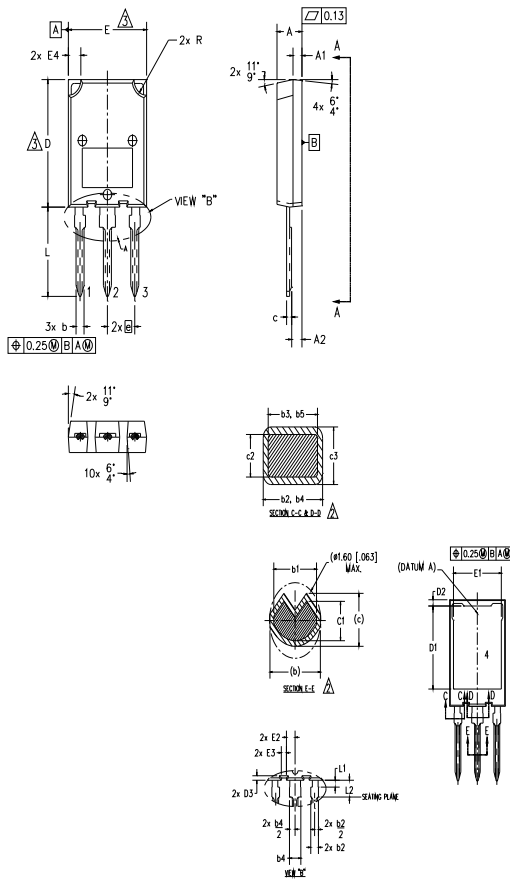
**Fig. WF3** - Typ. Diode Recovery Waveform  
@  $T_J = 175^\circ\text{C}$  using Fig. CT.4



**Fig. WF4** - Typ. S.C. Waveform  
@  $T_J = 150^\circ\text{C}$  using Fig. CT.3

# Super 247 Package Outline

Dimensions are shown in millimeters (inches)



**NOTES:**

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M-1994
2. DIMENSIONS b1, b3, b5, c1 & c3 APPLY TO BASE METAL ONLY.
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTER EXTREMES OF THE PLASTIC BODY.
4. ALL DIMENSIONS SHOWN IN MILLIMETERS.
5. CONTROLLING DIMENSION: MILLIMETER.
6. OUTLINE CONFORMS TO JEDEC OUTLINE TO-274AA

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.50	5.50	.177	.217	
A1	1.45	2.15	.057	.085	
A2	1.65	2.35	.065	.093	
b	1.45	1.60	.054	.063	
b1	1.40	1.50	.055	.059	2
b2	2.00	2.40	.079	.094	
b3	1.95	2.35	.077	.093	2
b4	3.00	3.15	.118	.124	
b5	2.95	3.35	.116	.132	2
c	1.10	1.30	.043	.051	
c1	0.90	1.10	.035	.043	2
c2	0.65	0.85	.026	.033	
c3	0.50	0.70	.020	.028	2
D	19.80	20.80	.780	.819	3
D1	15.50	16.10	.610	.634	
D2	0.70	1.30	.028	.051	
D3	0.75	1.25	.030	.049	
E	15.10	16.10	.594	.634	3
E1	13.30	13.90	.524	.547	
E2	2.25	2.70	.089	.109	
E3	1.20	1.70	.047	.067	
E4	2.00	3.00	.079	.118	
e	5.45 BSC		.215 BSC		
L	13.80	14.80	.535	.583	
L1	1.00	1.60	.039	.063	
L2	3.85	4.25	.152	.167	
R	2.00	3.00	.079	.118	

LEAD ASSIGNMENTS

MOSFET

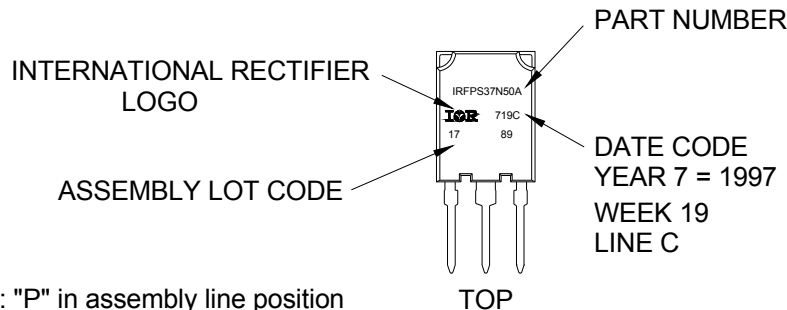
- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBT

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

## Super 247 Part Marking Information

EXAMPLE: THIS IS AN IRFPS37N50A WITH ASSEMBLY LOT CODE 1789 ASSEMBLED ON WW 19, 1997 IN THE ASSEMBLY LINE "C"



Note: "P" in assembly line position indicates "Lead-Free"

Super 247 package is not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

**Qualification Information<sup>†</sup>**

<b>Qualification Level</b>	Industrial	
<b>Moisture Sensitivity Level</b>	Super 247	N/A
<b>RoHS Compliant</b>	Yes	

† Qualification standards can be found at International Rectifier’s web site: <http://www.irf.com/product-info/reliability/>

†† Applicable version of JEDEC standard at the time of product release.

**Revision History**

<b>Date</b>	<b>Comments</b>
11/13/2014	<ul style="list-style-type: none"> <li>• Added I<sub>FM</sub> Diode Maximum Forward Current = 480A with the note ④ on page 1.</li> <li>• Removed note ④ from switching losses test condition on page 2.</li> </ul>

## Looking for pricing, stock, or lifecycle information?

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